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NON TECHNICAL CONTENT

Front cover and table of contents

Back cover

EDITORIAL

A. I. Bienenstock, C. W. Bates, and W. Spicer Some editorial comments 89

INVITED PAPERS

Stanford R. Ovshinsky and Hellmut Fritzsche Amorphous semiconductors for switching, memory, and imaging applications 91

Alan E. Owen and John M. Robertson Electronic conduction and switching in chalcogenide glasses 105

Anthony C. Warren Reversible thermal breakdown as a switching mechanism in chalcogenide glasses 123

Mark D. Tabak, Samuel W. Ing, and Merlin E. Scharfe Operation and performance of amorphous selenium-based photoreceptors 132

CONTRIBUTED PAPERS

Geof V. Bunton and R. M. Quilliam Switching and memory effects in amorphous chalcogenide thin films 140

Martin Regan and Cyril F. Drake Delay time measurement in transition metal oxide glass devices 144

S. Basavaiah and K. C. Park Bistable switching and conduction mechanisms in Nb-Nb₂O₅-Bi junctions 149

Andreas Csillag Accumulation effects in an amorphous chalcogenide thin-film switch 157

Arthur C. M. Chen Electron beam heating in amorphous semiconductor beam memory 160

M. P. Shaw, H. L. Grubin, and I. J. Gastman Analysis of an inhomogeneous bulk "S-shaped" negative differential conductivity element in a circuit containing reactive elements 169

Kenneth E. Van Landingham Circuit applications of Ovonic switching devices 178

Roy J. Zingg, Richard E. Zimmerman, and Arthur V. Pohn A terminal multiplexor application of Ovonic memories 188

R. G. Neale and John A. Aseltine The application of amorphous materials to computer memories 195